

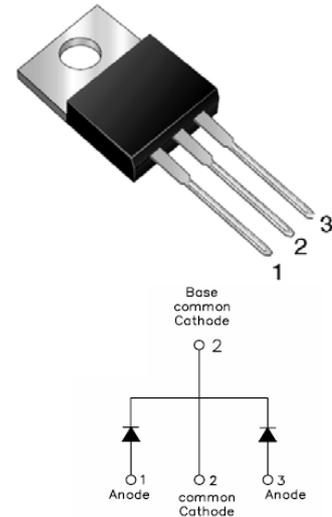
SBR20200CT SCHOTTKY RECTIFIER

Applications:

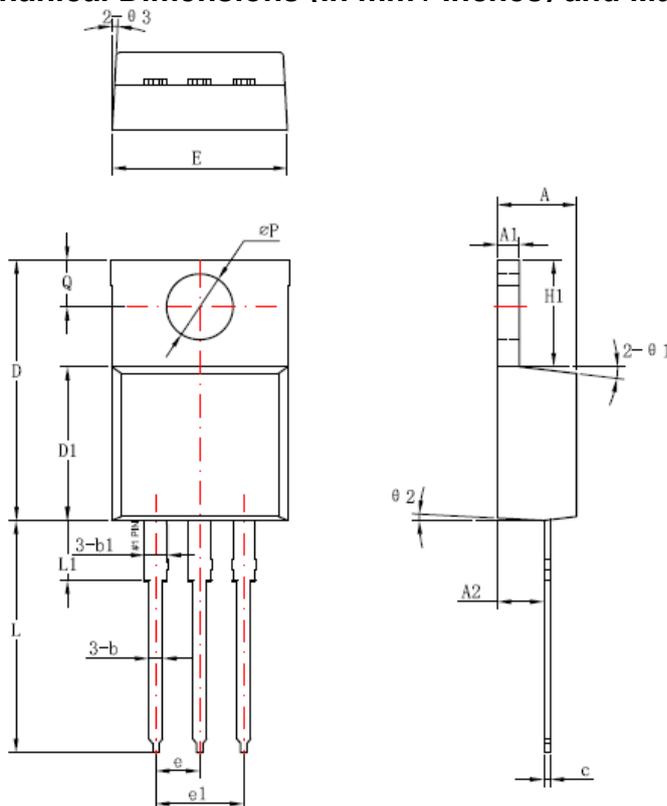
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

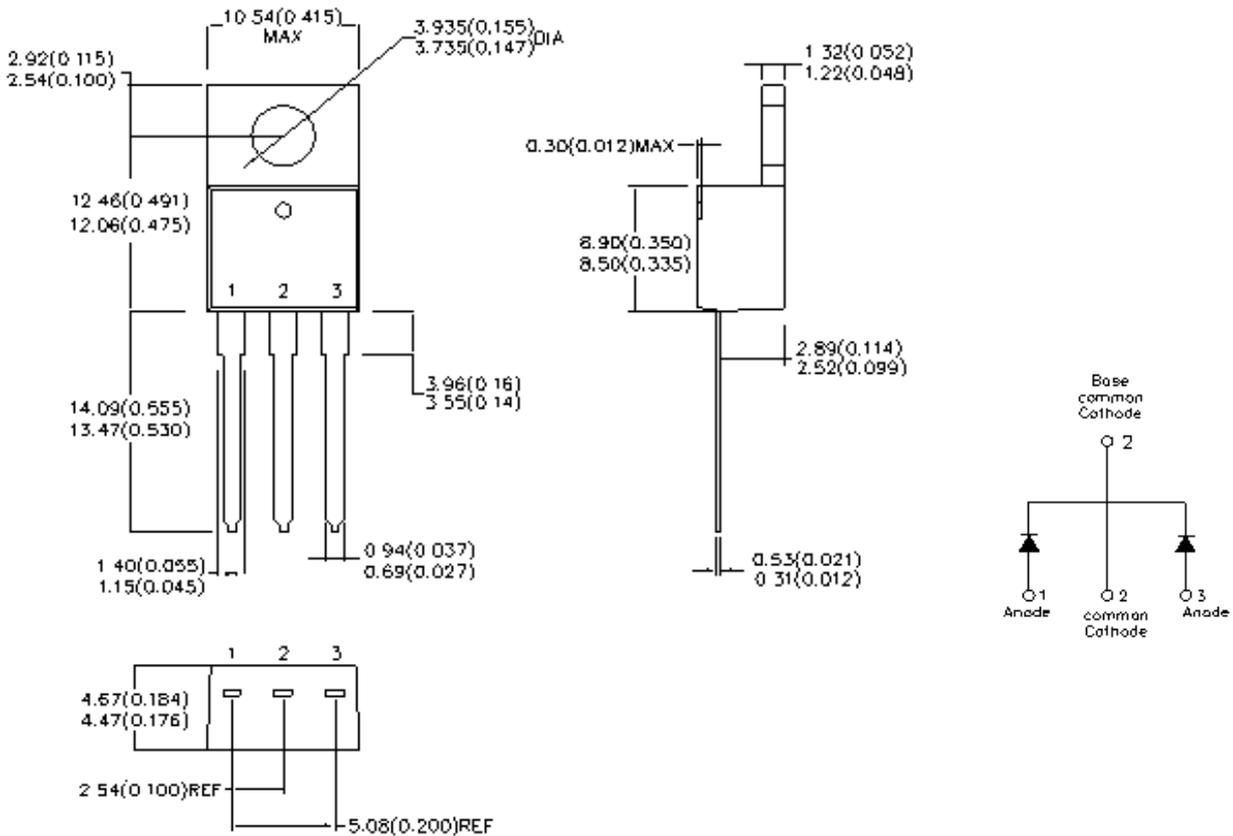


Mechanical Dimensions (In mm / Inches) and Marking:



| Symbol | Dimensions in millimeters | | |
|--------|---------------------------|---------|-------|
| | Min | Typical | Max |
| A | 4.42 | 4.57 | 4.72 |
| A1 | 1.17 | 1.27 | 1.37 |
| A2 | 2.59 | 2.69 | 2.89 |
| b | 0.71 | 0.81 | 0.96 |
| b1 | | 1.27 | |
| c | 0.36 | 0.38 | 0.61 |
| D | 14.94 | 15.24 | 15.54 |
| D1 | 8.85 | 9.00 | 9.15 |
| E | 10.01 | 10.16 | 10.31 |
| e | | 2.54 | |
| e1 | | 5.06 | |
| H1 | 6.04 | 6.24 | 6.44 |
| L | 12.7 | 13.56 | 13.78 |
| L1 | | 3.5 | |
| ΦP | 3.74 | 3.84 | 4.04 |
| Q | 2.54 | 2.74 | 2.94 |
| θ1 | | 7° | |
| θ2 | | 3° | |
| θ3 | | 4° | |

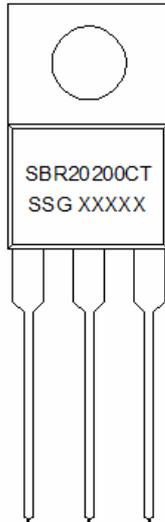
OPTION1 (HD)



OPTION2 (CJ)

TO-220AB

Marking Diagram:



Where XXXXX is YYWWL

- SBR = Device Type
- 20 = Forward Current (20A)
- 200 = Reverse Voltage (200V)
- CT = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

| Device | Package | Shipping |
|------------|--------------------|---------------|
| SBR20200CT | TO-220AB (Pb-Free) | 50 pcs / tube |

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

| Characteristics | Symbol | Condition | Max. | Units |
|---|-------------|--|------|-------|
| Peak Inverse Voltage | V_{RWM} | - | 200 | V |
| Average Forward Current (per device) | $I_{F(AV)}$ | 50% duty cycle @ $T_C = 150^\circ\text{C}$, rectangular wave form | 20 | A |
| Peak One Cycle Non-Repetitive Surge Current (per leg) | I_{FSM} | 8.3 ms, half Sine pulse | 120 | A |

Electrical Characteristics:

| Characteristics | Symbol | Condition | Max. | Units |
|----------------------------------|----------|---|------|-------|
| Forward Voltage Drop (per leg) * | V_{F1} | @ 10 A, Pulse, $T_C = 25\text{ }^\circ\text{C}$ | 0.95 | V |
| | V_{F2} | @ 10 A, Pulse, $T_C = 125\text{ }^\circ\text{C}$ | 0.85 | V |
| Reverse Current (per leg) * | I_{R1} | @ $V_R = \text{rated } V_R$ $T_C = 25\text{ }^\circ\text{C}$ | 1.0 | mA |
| Junction Capacitance (per leg) | C_T | @ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$ | 150 | pF |

* Pulse Width < 300 μ s, Duty Cycle <2%

Thermal-Mechanical Specifications:

| Characteristics | Symbol | Condition | Specification | Units |
|---|-----------------|--------------|---------------|--------------------|
| Junction Temperature | T_J | - | -55 to +150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | - | -55 to +150 | $^\circ\text{C}$ |
| Maximum Thermal Resistance Junction to Case | $R_{\theta JC}$ | DC operation | 3.5 | $^\circ\text{C/W}$ |
| Approximate Weight | wt | - | 2 | g |
| Case Style | TO-220AB | | | |

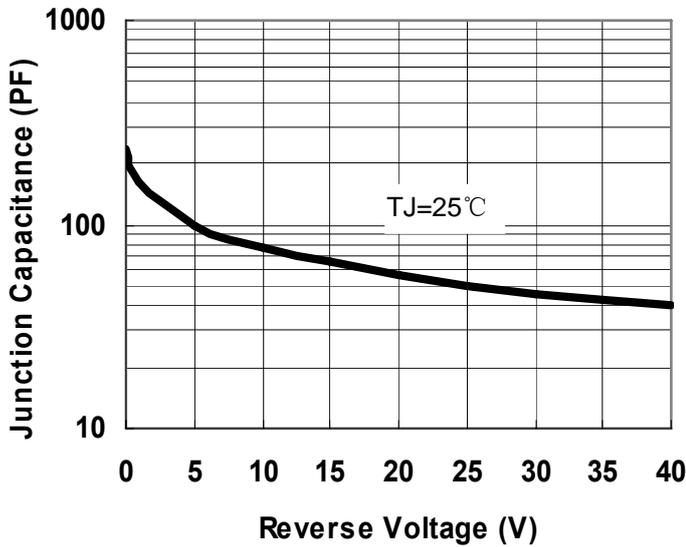


Fig.1-Typical Junction Capacitance

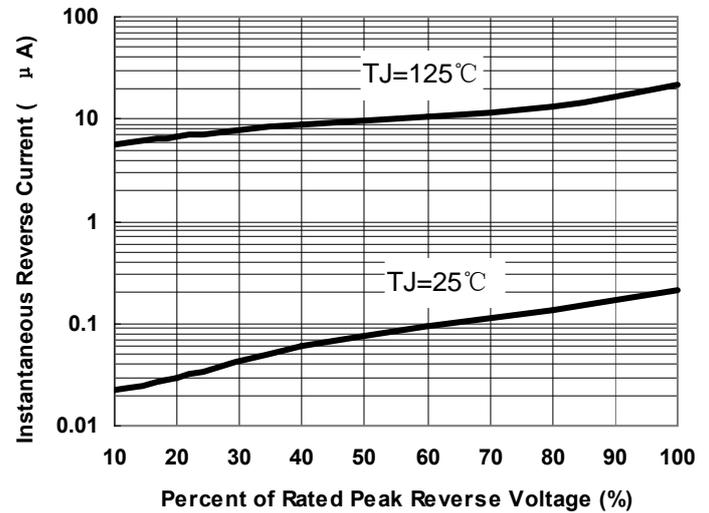


Fig.2-Typical Reverse Characteristics

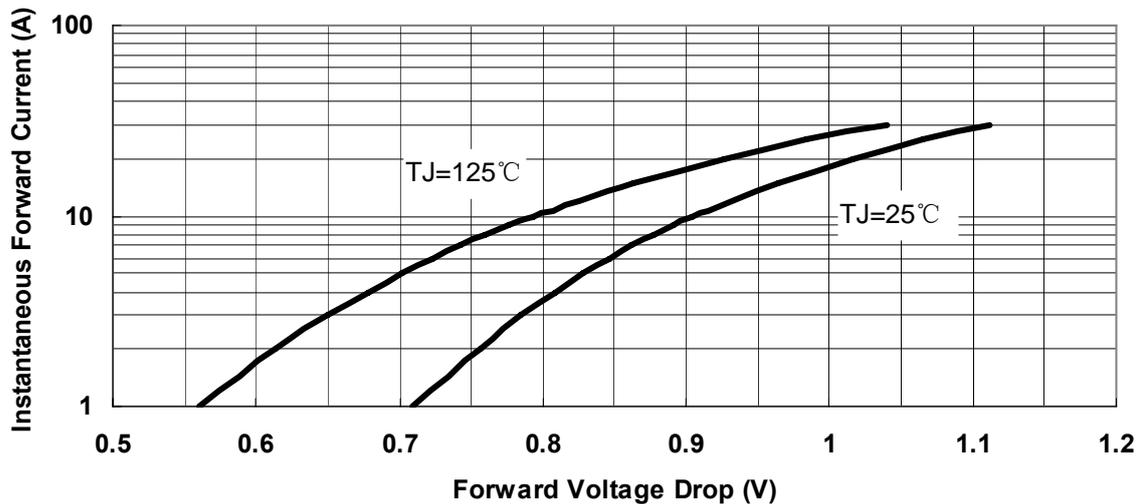


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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